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(57) Abstract :

The present disclosure relates to a device (100) comprising one or more n-channel metal-oxide semiconductor (NMOS) transistors comprising a first NMOS transistor (102-1) and a second NMOS transistor (102-2), input signal to be filtered is applied to gate terminal of the first NMOS transistor (102-1) and one or more P-channel metal-oxide-semiconductor (PMOS) transistors comprising a first PMOS transistor (104-1), a second p-channel metal-oxide semiconductor (PMOS) transistor (104-2) and a third PMOS transistor (104-3), the filtered output is obtained between source terminal and drain terminal of the second PMOS transistor and the third PMOS transistor respectively, wherein the one or more NMOS transistors and the one or more PMOS transistors are arranged in such a manner to reduce noise values of biomedical signals.

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